Ordering number : ENN7088

N-channel Silicon Junction FET

TF218

Capacitor Microphone Applications

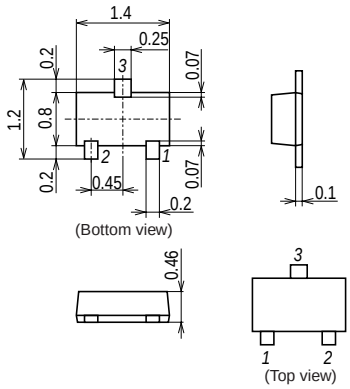
Features

- Ultrasmall package facilitates miniaturization in end products.
- Especially suited for use in audio, telephone capacitor microphones.
- Excellent voltage characteristic.
- Excellent transient characteristic.
- Adoption of FBET process.

Package Dimensions

unit : mm
2201

[TF218]



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Gate-to-Drain Voltage	V_{GDO}		−20	V
Gate Current	I_G		10	mA
Drain Current	I_D		1	mA
Allowable Power Dissipation	P_D		100	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDO}$	I_G=−100μA	−20			V
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=5V, I_D=1μA	−0.2	−0.6	−1.0	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=5V, V_{GS}=0	140*		350*	μA
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=5V, V_{GS}=0, f=1kHz	0.5	1.0		mS
Input Capacitance	Ciss	V_{DS}=5V, V_{GS}=0, f=1MHz		3.5		pF
Reverse Transfer Capacitance	Crss	V_{DS}=5V, V_{GS}=0, f=1MHz		0.65		pF

Continued on next page.

* : The TF218 is classified by I_{DSS} as follows : (unit : μA)

Marking	A4	A5
I_{DSS}	140 to 240	210 to 350

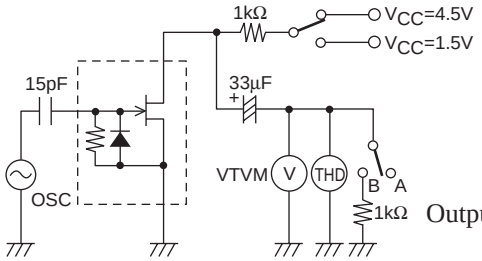
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Continued from preceding page.

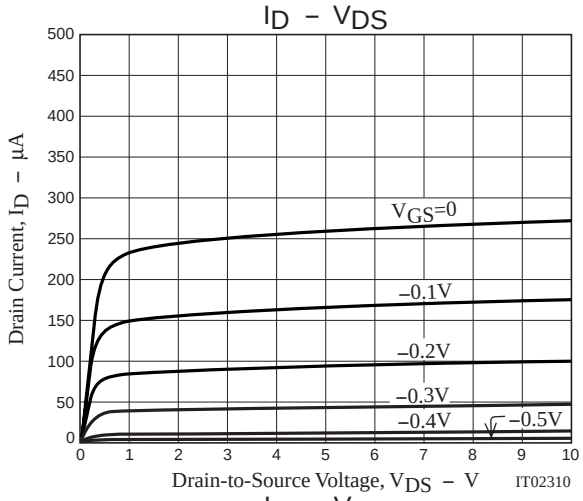
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[Ta=25°C, V_{CC}=4.5V, R_L=1kΩ, Cin=15pF, See specified Test Circuit.]						
Voltage Gain	G_V	V_{IN}=10mV, f=1kHz		-3.0		dB
Reduced Voltage Characteristic	ΔG_{VV}	V_{IN}=10mV, f=1kHz, V_{CC}=4.5→1.5V		-1.2	-3.5	dB
Frequency Characteristic	ΔGvf	f=1kHz to 110Hz			-1.0	dB
Input Impedance	Z_{IN}	f=1kHz	25			MΩ
Output Impedance	Z_O	f=1kHz		1000		Ω
Total Harmonic Distortion	THD	V_{IN}=30mV, f=1kHz		1.2		%
Output Noise Voltage	V_{NO}	V_{IN}=0, A curve			-110	dB

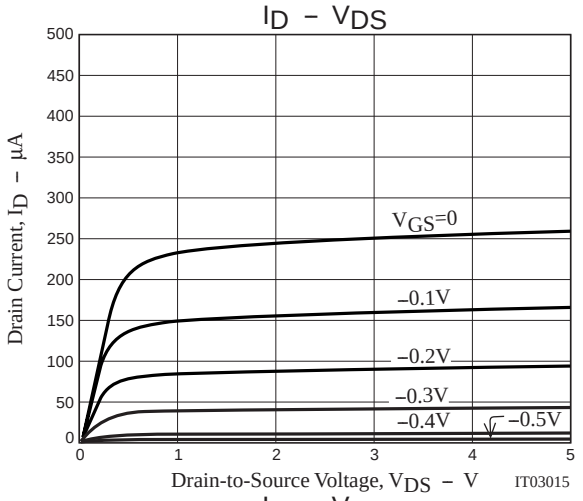
Test Circuit

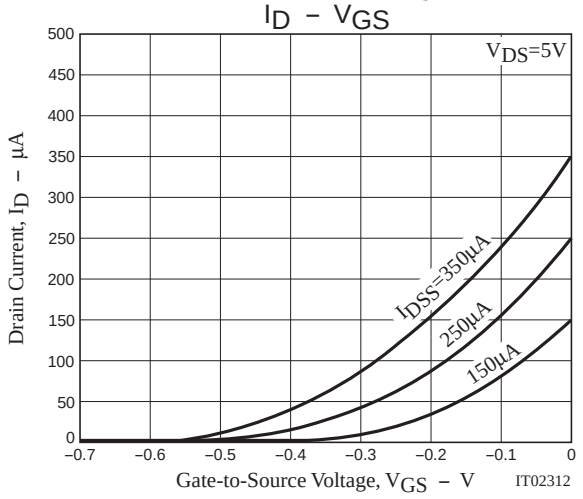
Voltage gain
Frequency Characteristic
Distortion
Reduced Voltage Characteristic

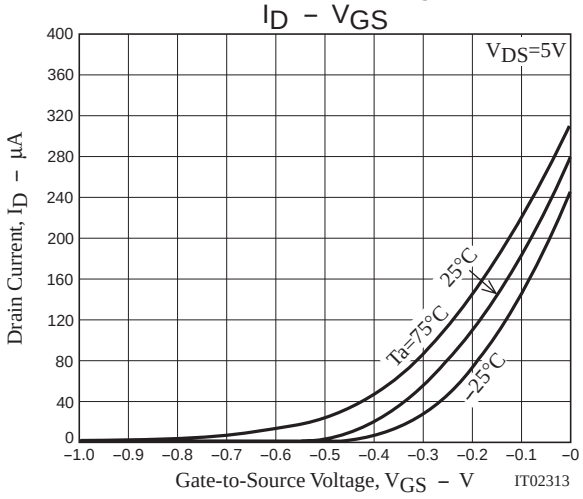


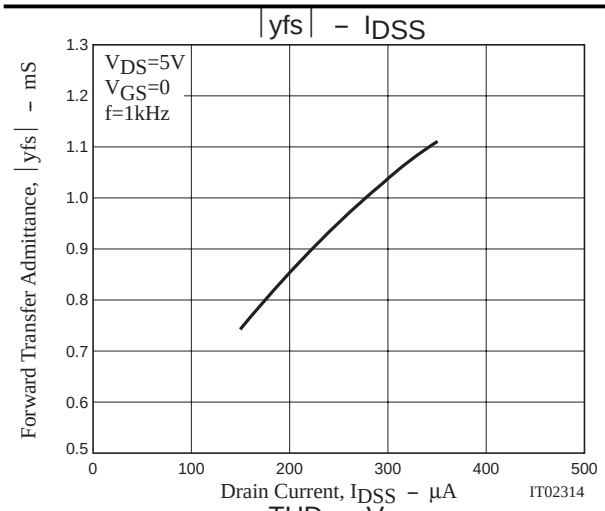
Output Impedance

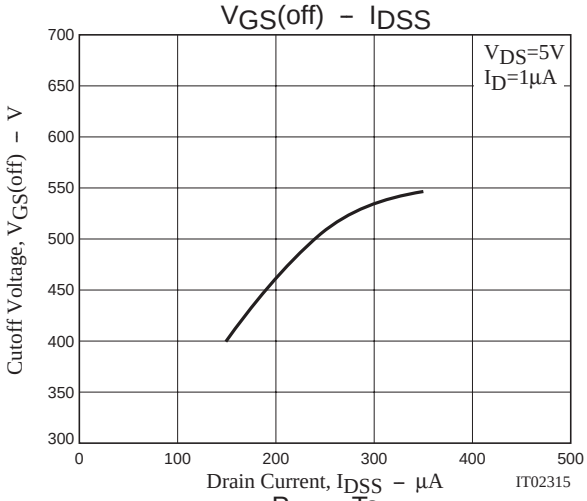


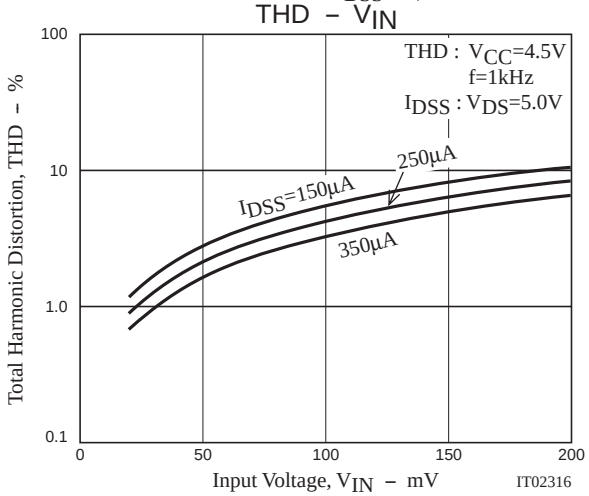


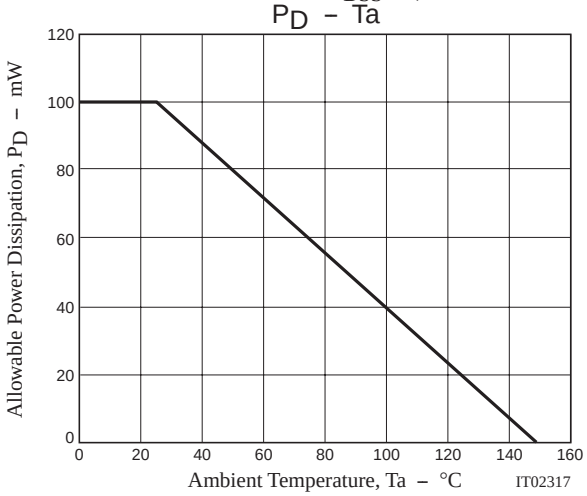


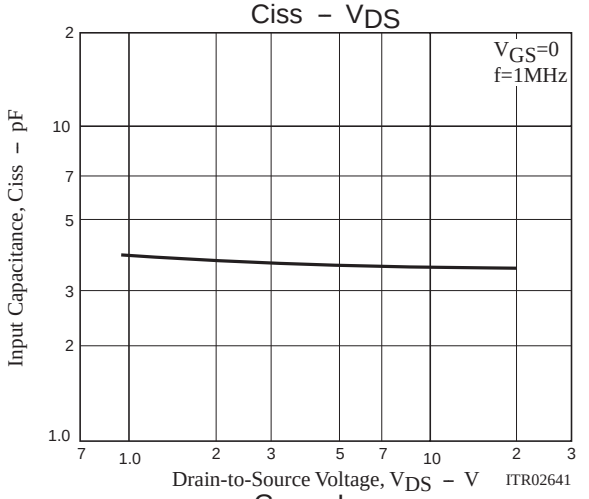


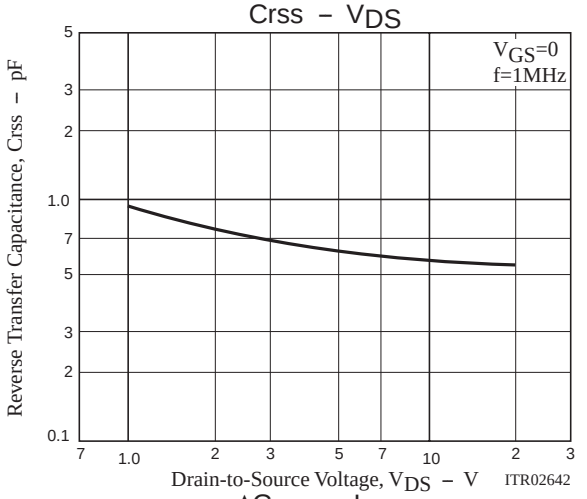

|yfs| – IDSS
VDS=5V
VGS=0
f=1kHz
Forward Transfer Admittance, |yfs| – mS
Drain Current, IDSS – µA
IT02314

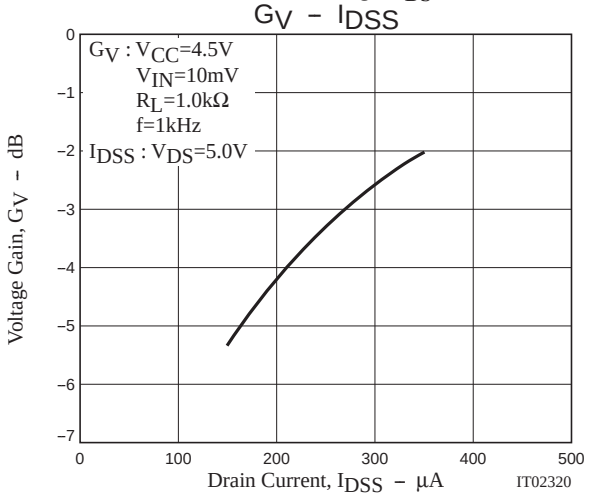

VGS(off) – IDSS
VDS=5V
ID=1µA
Cutoff Voltage, VGS(off) – V
Drain Current, IDSS – µA
IT02315

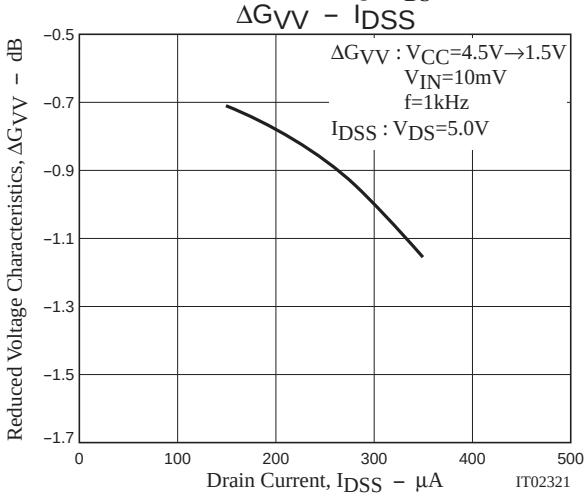

THD – VIN
THD : VCC=4.5V
f=1kHz
IDSS : VDS=5.0V
250µA
IDSS=150µA
350µA
Total Harmonic Distortion, THD – %
Input Voltage, VIN – mV
IT02316


PD – Ta
Allowable Power Dissipation, PD – mW
Ambient Temperature, Ta – °C
IT02317


Ciss – VDS
VGS=0
f=1MHz
Input Capacitance, Ciss – pF
Drain-to-Source Voltage, VDS – V
ITR02641


Crss – VDS
VGS=0
f=1MHz
Reverse Transfer Capacitance, Crss – pF
Drain-to-Source Voltage, VDS – V
ITR02642


GV – IDSS
GV : VCC=4.5V
VIN=10mV
RL=1.0kΩ
f=1kHz
IDSS : VDS=5.0V
Voltage Gain, GV – dB
Drain Current, IDSS – µA
IT02320


ΔGVV – IDSS
ΔGVV : VCC=4.5V→1.5V
VIN=10mV
f=1kHz
IDSS : VDS=5.0V
Reduced Voltage Characteristics, ΔGVV – dB
Drain Current, IDSS – µA
IT02321